

PTO/SB/08B (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	10/649,712
Filing Date	August 26, 2003
First Named Inventor	Ren, Fan
Art Unit	2812
Examiner Name	
Attorney Docket Number	5853-274

Sheet	1	of	1
-------	---	----	---

NON PATENT LITERATURE DOCUMENTS

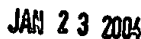
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Kim et al., "Inversion behavior in Sc2O3/GaN gated diodes," Appl. Phys. Lett., 81: 373-375, July 2002.	
		Simin et al., "7.5KW/mm2 current switch using AlGaIn/GaN metal-oxide-semiconductor heterostructure field effect transistor on SiC substrates," Electronics Letters, 36: November 2000.	
		Mistele et al., "First AlGaIn/GaN MOSFET with photoanodic gate dielectric," Materials Science and Engineering, B93, 107-111, 2002.	
		Khan et al., "Enhancement and depletion mode GaN/AlGaIn heterostructure field effect transistors," Appl. Phys. Lett., 68: 514-516, January 1996.	
		Simin, et al., "SiO2/AlGaIn/InGaIn/GaN MOSDHFTs," IEEE Electron Device Letters, 23: 458-460, August 2002.	
		Kim et al., "Characteristics of MgO/GaN gate-controlled metal-oxide-semiconductor diodes," Applied Physics Letter, 80: 4555-4557, June 2002.	
		Koudymov et al., "Maximum current in nitride-based heterostructure field-effect transistors," Applied Physics Letters, 80: 3216-3218, April 2002.	
		Hu et al., "Si3N4/AlGaIn/GaN-metal-insulator-semiconductor heterostructure field-effect transistors," Applied Physics Letters, 79: 2832-2834, October 2001.	
		Teles et al., "Spinodal decomposition in BxGa1-xN and BxAl1-xN alloys," Applied Physics Letters, 80: 1177-1179, February 2002.	
		Chou et al., AlGaIn/GaN Metal Oxide Semiconductor Heterostructure Field-Effect Transistor Based on a Liquid Phase Deposited Oxide," Jpn. J. Appl. Phys. 41: L748-L750, July 2002.	

Examiner
SignatureDate
Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.



Approved for use through 07/31/2006. OMB 0651-0031

Approved for use through 07/31/2008. OMB 0051-0001
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
This document contains a valid OMB control number.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. **Complete if Known**

Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet	1	of	1
-------	---	----	---

Complete if Known

Application Number	10/649,712
Filing Date	August 26, 2003
First Named Inventor	Ren, Fan
Art Unit	2812
Examiner Name	
Attorney Docket Number	5853-274

U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

**Examiner
Signature**

Date
Considered

Examiner Signature	<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language translation is attached.</p>
--------------------	---

Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. **DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

When completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.